

Current Transducers HAS 50..600-P

For the electronic measurement of currents: DC, AC, pulsed, mixed, with a galvanic isolation between the primary circuit (high power) and the secondary circuit (electronic circuit).

 $I_{PN} = 50..600 A$

 $V_{OUT} = \pm 4 V$





Electrical data							
Primary nominar.m.s. current	al Primary current measuring range I _P (A)	Туре					
50 100 200 300 400 500	±150 ±300 ±600 ±900 ±900 ±900	HAS 50-P HAS 100-P HAS 200-P HAS 300-P HAS 400-P HAS 500-P					
V _c	±900 Supply voltage (± 5 %) Current consumption	HAS 600-P	±15 ±15	V mA			
$egin{array}{l}_{c} \\ oldsymbol{I}_{oc} \\ oldsymbol{V}_{d} \\ oldsymbol{K}_{ls} \\ oldsymbol{V}_{out} \\ oldsymbol{R}_{out} \\ oldsymbol{R}_{l} \end{array}$	Overload capacity R.m.s. voltage for AC isolat R.m.s. rated voltage, safe s Isolation resistance @ 500 Output voltage @ ± I _{PN} , R _L = Output internal resistance Load resistance	separation VDC	30,000 3 500 ¹⁾ > 1000 ±4V ±40 100 > 1	At kV V MΩ mV Ω kΩ			

uracy - Dynamic performance data		
Accuracy @ I_{PN} , $T_{A} = 25^{\circ}C$ (without offset)	< ±1	%
Linearity $^{2)}$ $(0\pm 1_{PN})$	< ±1	% of I _{PN}
Electrical offset voltage, $T_{A} = 25^{\circ}C$	< ±40	m̈̈V
Hysteresis offset voltage $\hat{\mathbb{Q}} _{PN} \rightarrow 0$	< ±20	mV
Thermal drift of V _{OF} HAS 50-P	< ±2	mV/K
HAS 100600-P	< ±1	mV/K
Thermal drift of the gain (% of reading)	< ±0.1	%/K
Response time @ 90% of I_P	< 3	μs
di/dt accurately followed	> 50	A/μs
Frequency bandwidth (small signal, -1dB) 3) 4)	DC 25	6 kHz
	Electrical offset voltage, $\mathbf{T}_{\mathrm{A}} = 25^{\circ}\mathrm{C}$ Hysteresis offset voltage @ $\mathbf{I}_{\mathrm{PN}} \rightarrow 0$ Thermal drift of \mathbf{V}_{OE} HAS 50-P HAS 100600-P Thermal drift of the gain (% of reading) Response time @ 90% of \mathbf{I}_{P} di/dt accurately followed	Accuracy @ \mathbf{I}_{PN} , $\mathbf{T}_{\text{A}} = 25^{\circ}\text{C}$ (without offset) < ± 1 Linearity 2) (0 $\pm \mathbf{I}_{\text{PN}}$) < ± 1 Electrical offset voltage, $\mathbf{T}_{\text{A}} = 25^{\circ}\text{C}$ < ± 40 Hysteresis offset voltage @ $\mathbf{I}_{\text{PN}} \rightarrow 0$ < ± 20 Thermal drift of \mathbf{V}_{OE} HAS 50-P < ± 2 HAS 100600-P < ± 1 Thermal drift of the gain (% of reading) < ± 0.1 Response time @ 90% of \mathbf{I}_{P} < 3 di/dt accurately followed > 50

	General data					
T _A T _S m	Ambient operating temperature Ambient storage temperature Mass approx. Standards 5)	- 25 + 85 - 25 + 85 80 EN 50082-2	°C g			

Notes: 1) Pollution class 2, overvoltage category III.

- ²⁾ Linearity data exclude the electrical offset.
- ³⁾ Please refer to derating curves in the technical file to avoid excessive core heating at high frequency.
- ⁴⁾ Amorphous core option for high frequency application.
- ⁵⁾ Please consult characterisation report for more technical details and application advice.

Features

- Hall effect measuring principle
- Galvanic isolation between primary and secondary circuit
- Isolation voltage 3000 V~
- Low power consumption
- Extended measuring range (3 x I_{PN})
- Insulated plastic case made of polycarbonate PBT recognized according to UL 94-V0
- Right angle pins for direct PCB mounting

Advantages

- Easy mounting
- Small size and space saving
- Only one design for wide current ratings range
- High immunity to external interference.

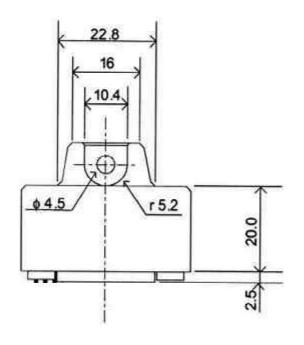
Applications

- AC variable speed drives
- Static converters for DC motor drives
- Battery supplied applications
- Uninterruptible Power Supplies (UPS)
- Switched Mode Power Supplies (SMPS)
- Power supplies for welding applications.

040406/0



HAS 50..600-P Dimensions (in mm)



PINS ARRANGEMENT

- 1. +15V
- 2. -15V
- 3. OUTPUT
- 4. 0V

